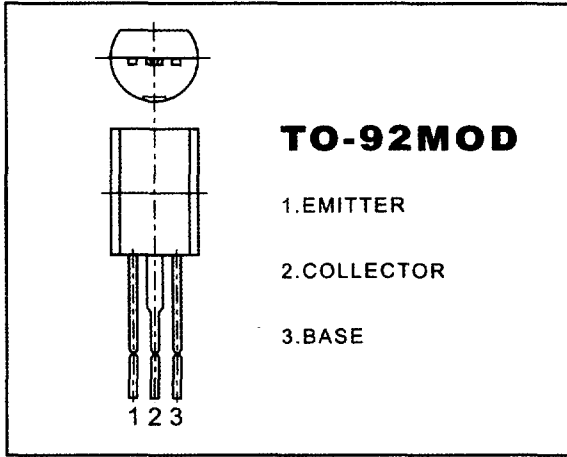


TO-92MOD Plastic-Encapsulate Transistors

2SC2236 TRANSISTOR(NPN)



FEATURES

- **Power dissipation**
P_{CM}: 0.9W (T_{amb}=25°C)
- **Collector current**
I_{CM}: 1.5 A
- **Collector-base voltage**
V_{(BR)CBO}: 30 V
- **Operating and storage junction temperature range**
T_J, T_{stg}: -55°C to + 150°C

ELECTRICAL CHARACTERISTICS

(T_{amb}=25°C unless otherwise specified)

Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1 mA, I _E = 0	30		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10 mA, I _B = 0	30		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 1 mA, I _C = 0	5		V
Collector cut-off current	I _{CBO}	V _{CB} = 30 V, I _E = 0		0.1	μ A
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0		0.1	μ A
DC current gain	h _{FE}	V _{CE} = 2 V, I _C = 500 mA	100	320	
Collector-emitter saturation voltage	V _{CEsat}	I _C = 1.5 A, I _B = 0.03 A		2	V
Base-emitter voltage	V _{BE}	I _C = 500 mA, V _{CE} = 2 V		1	V
Transition frequency	f _T	V _{CE} = 2 V, I _C = 500 mA	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320

Typical Characteristics

2SC2236

